

Amendments to the Abstract

Please replace the subtitle and text of the Abstract as follows:

Abstract of the Disclosure

Silicon nitride film is formed on substrate (112) by feeding trisilylamine and ammonia into a CVD reaction chamber (11) that contains a substrate (112). The ammonia gas/trisilylamine gas flow rate ratio is set to a value of at least about 10 and/or the thermal CVD reaction is run at a temperature no greater than about 600°C. Silicon oxynitride is obtained by introducing an oxygen source gas into the CVD reaction chamber (11). This method avoids the production of ammonium chloride and/or the incorporation of carbonaceous contaminants which are detrimental to the quality of the deposited film.